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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 19x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f091rct6j

List of figures

Table 2. STM32F091xB/xC family device features and peripheral counts

Peripheral		STM32F091Cx		STM32F091Rx		STM32F091Vx	
Flash memory (Kbyte)		128	256	128	256	128	256
SRAM (Kbyte)		32					
Timers	Advanced control	1 (16-bit)					
	General purpose	5 (16-bit) 1 (32-bit)					
	Basic	2 (16-bit)					
Comm. interfaces	SPI [I^2S](1)	2 [2]					
	I^2C	2					
	USART	6		8			
	CAN	1					
	CEC	1					
12-bit ADC (number of channels)		1 (10 ext. + 3 int.)		1 (16 ext. + 3 int.)			
12-bit DAC (number of channels)		1 (2)					
Analog comparator		2					
GPIOs		38		52		88	
Capacitive sensing channels		17		18		24	
Max. CPU frequency		48 MHz					
Operating voltage		2.0 to 3.6 V					
Operating temperature		Ambient operating temperature: -40°C to 85°C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C					
Packages		LQFP48 UFQFPN48		LQFP64 UFBGA64 WLCSP64		LQFP100 UFBGA100	

1. The SPI interface can be used either in SPI mode or in I^2S audio mode.

verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C peripherals can be served by the DMA controller.

Refer to *Table 9* for the differences between I2C1 and I2C2.

Table 9. STM32F091xB/xC I^2C implementation

I^2C features(1)	I2C1	I2C2
7-bit addressing mode	X	X
10-bit addressing mode	X	X
Standard mode (up to 100 kbit/s)	X	X
Fast mode (up to 400 kbit/s)	X	X
Fast Mode Plus (up to 1 Mbit/s) with 20 mA output drive I/Os	X	X
Independent clock	X	-
SMBus	X	-
Wakeup from STOP	X	-

1. X = supported.

3.17 Universal synchronous/asynchronous receiver/transmitter (USART)

The device embeds up to eight universal synchronous/asynchronous receivers/transmitters (USART1, USART2, USART3, USART4, USART5, USART6, USART7, USART8) which communicate at speeds of up to 6 Mbit/s.

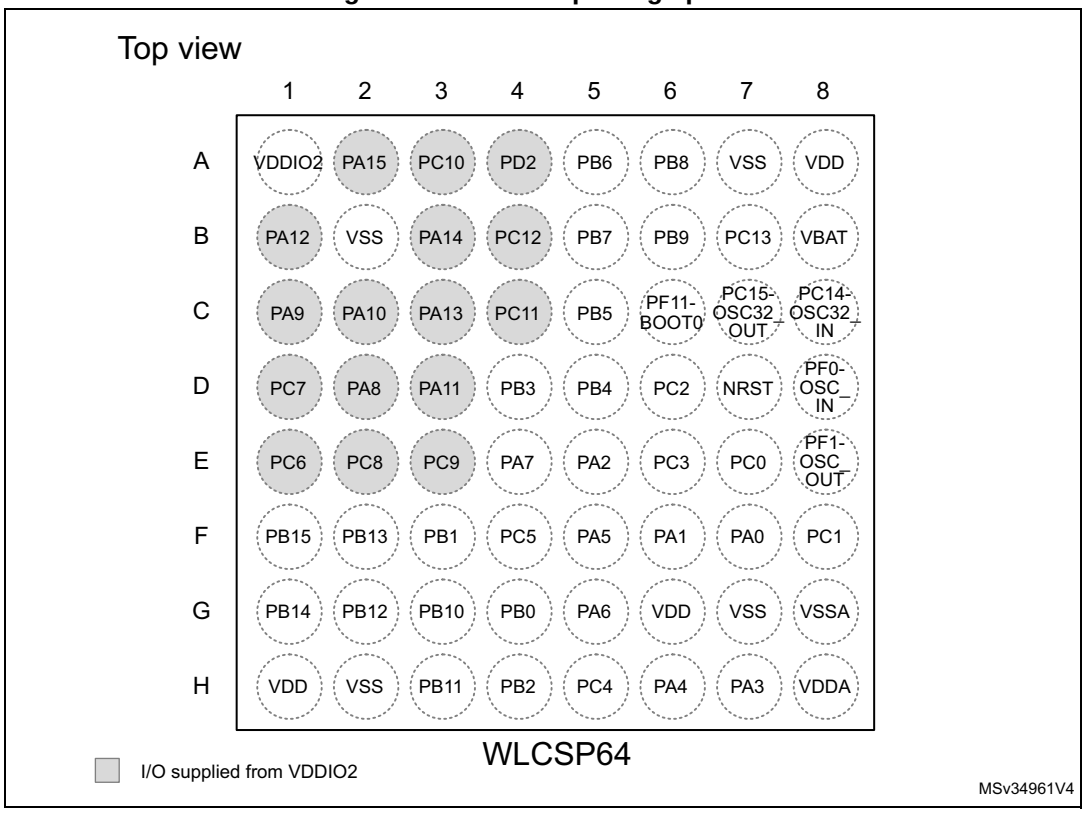
They provide hardware management of the CTS, RTS and RS485 DE signals, multiprocessor communication mode, master synchronous communication and single-wire half-duplex communication mode. USART1, USART2 and USART3 support also SmartCard communication (ISO 7816), IrDA SIR ENDEC, LIN Master/Slave capability and auto baud rate feature, and have a clock domain independent of the CPU clock, allowing to wake up the MCU from Stop mode.

The USART interfaces can be served by the DMA controller.

Table 10. STM32F091xB/xC USART implementation

USART modes/features(1)	USART1 USART2 USART3	USART4	USART5 USART6 USART7 USART8
Hardware flow control for modem	X	X	-
Continuous communication using DMA	X	X	X
Multiprocessor communication	X	X	X
Synchronous mode	X	X	X
Smartcard mode	X	-	-

Figure 7. WLCSP64 package pinout



1. The above figure shows the package in top view, changing from bottom view in the previous document versions.

Figure 8. LQFP48 package pinout

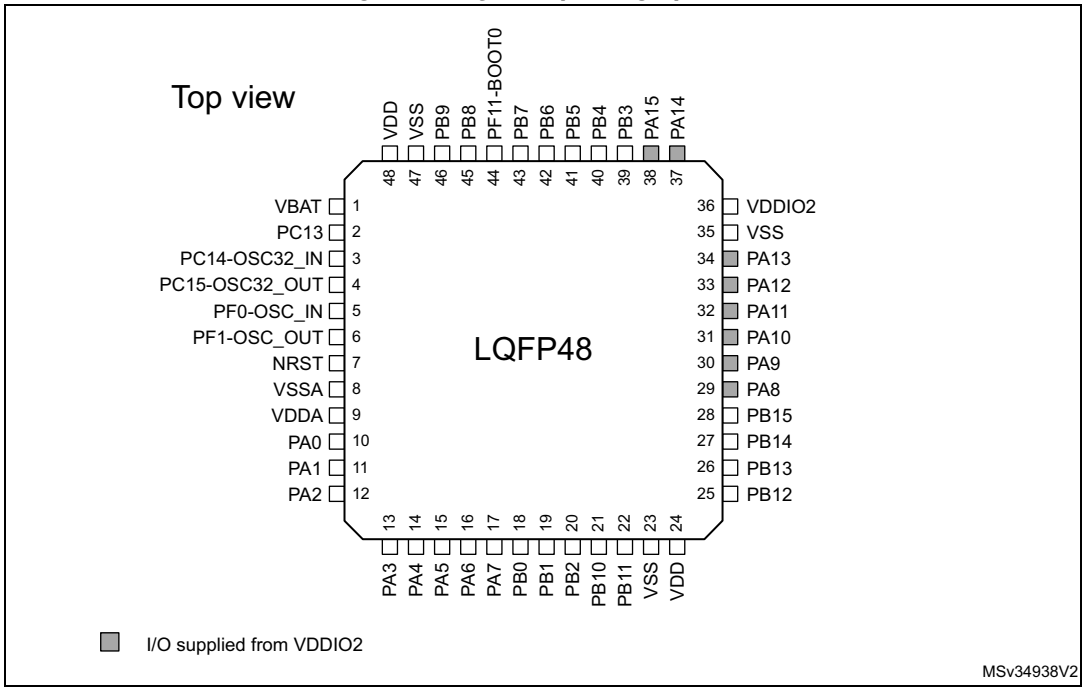


Figure 9. UFQFPN48 package pinout

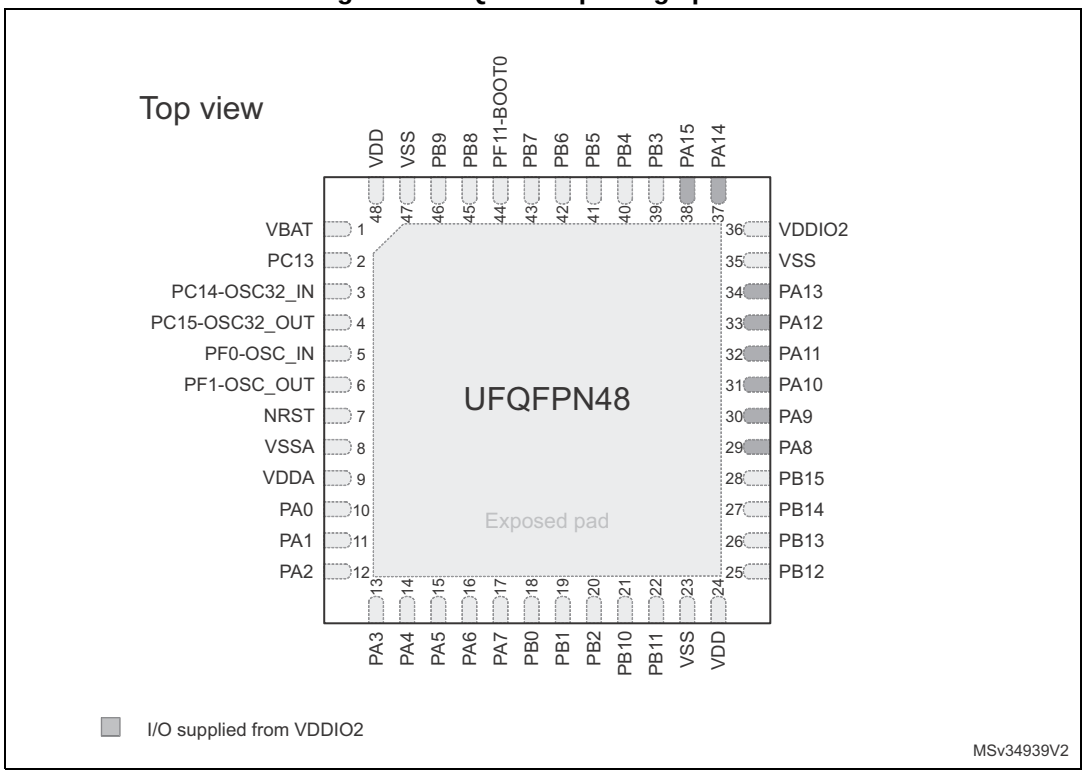


Table 12. Legend/abbreviations used in the pinout table

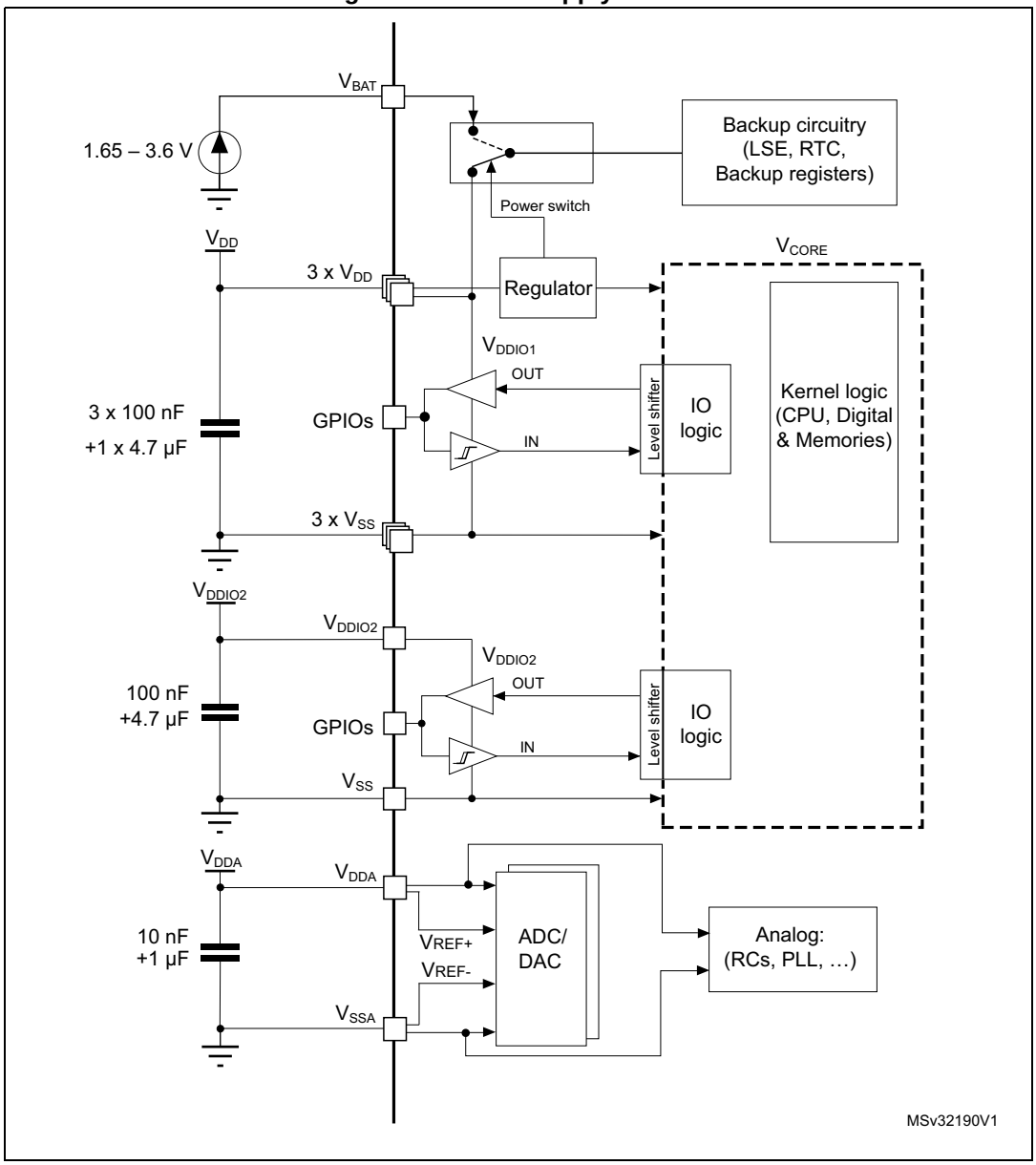
Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I/O	Input / output pin
I/O structure		FT	5 V-tolerant I/O
		FTf	5 V-tolerant I/O, FM+ capable
		TTa	3.3 V-tolerant I/O directly connected to ADC
		TC	Standard 3.3 V I/O
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 13. STM32F091xB/xC pin definitions (continued)

Pin numbers						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
UFBGA100	LQFP100	UFBGA64	LQFP64	WLCSP64	LQFP48/UFQFPN48					Alternate functions	Additional functions
J1	19	-	-	-	-	PF2	I/O	FT		EVENTOUT, USART7_TX, USART7_CK_RTS	WKUP8
K1	20	F1	12	G8	8	VSSA	S	-		Analog ground	
M1	21	H1	13	H8	9	VDDA	S	-		Analog power supply	
L1	22	-	-	-	-	PF3	I/O	FT		EVENTOUT, USART7_RX, USART6_CK_RTS	
L2	23	G2	14	F7	10	PA0	I/O	TTa		USART2_CTS, TIM2_CH1_ETR, TSC_G1_IO1, USART4_TX COMP1_OUT	RTC_ TAMP2, WKUP1, ADC_IN0, COMP1_INM6
M2	24	H2	15	F6	11	PA1	I/O	TTa		USART2_RTS, TIM2_CH2, TIM15_CH1N, TSC_G1_IO2, USART4_RX, EVENTOUT	ADC_IN1, COMP1_INP
K3	25	F3	16	E5	12	PA2	I/O	TTa		USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3 COMP2_OUT	ADC_IN2, WKUP4, COMP2_INM6
L3	26	G3	17	H7	13	PA3	I/O	TTa		USART2_RX,TIM2_CH4, TIM15_CH2, TSC_G1_IO4	ADC_IN3, COMP2_INP
D3	27	C2	18	G7	-	VSS	S	-		Ground	
H3	28	D2	19	G6	-	VDD	S	-		Digital power supply	
M3	29	H3	20	H6	14	PA4	I/O	TTa		SPI1_NSS, I2S1_WS, TIM14_CH1, TSC_G2_IO1, USART2_CK, USART6_TX	COMP1_INM4, COMP2_INM4, ADC_IN4, DAC_OUT1
K4	30	F4	21	F5	15	PA5	I/O	TTa		SPI1_SCK, I2S1_CK, CEC, TIM2_CH1_ETR, TSC_G2_IO2, USART6_RX	COMP1_INM5, COMP2_INM5, ADC_IN5, DAC_OUT2

6.1.6 Power supply scheme

Figure 13. Power supply scheme



Caution: Each power supply pair (V_{DD}/V_{SS}, V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 21: Voltage characteristics*, *Table 22: Current characteristics* and *Table 23: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 21. Voltage characteristics(1)

Symbol	Ratings	Min	Max	Unit
V_{DD}–V_{SS}	External main supply voltage	- 0.3	4.0	V
V_{DDIO2}–V_{SS}	External I/O supply voltage	- 0.3	4.0	V
V_{DDA}–V_{SS}	External analog supply voltage	- 0.3	4.0	V
V_{DD}–V_{DDA}	Allowed voltage difference for $V_{DD} > V_{DDA}$	-	0.4	V
V_{BAT}–V_{SS}	External backup supply voltage	- 0.3	4.0	V
V_{IN}(2)	Input voltage on FT and FTf pins	V_{SS} - 0.3	V_{DDIOx} + 4.0 (3)	V
	Input voltage on TTa pins	V_{SS} - 0.3	4.0	V
	Input voltage on any other pin	V_{SS} - 0.3	4.0	V
$\lvert\Delta V_{DDx}\rvert$	Variations between different V_{DD} power pins	-	50	mV
$\lvert V_{SSx} - V_{SS}\rvert$	Variations between all the different ground pins	-	50	mV
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.12: Electrical sensitivity characteristics*		-

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to for the maximum allowed injected current values.
3. Valid only if the internal pull-up/pull-down resistors are disabled. If internal pull-up or pull-down resistor is enabled, the maximum limit is 4 V.

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 39. HSE oscillator characteristics

Symbol	Parameter	Conditions[1]	Min[2]	Typ	Max[2]	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup[3]	-	-	8.5	mA
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.4	-	
		V_{DD} = 3.3 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.5	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$[4]	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design, not tested in production.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

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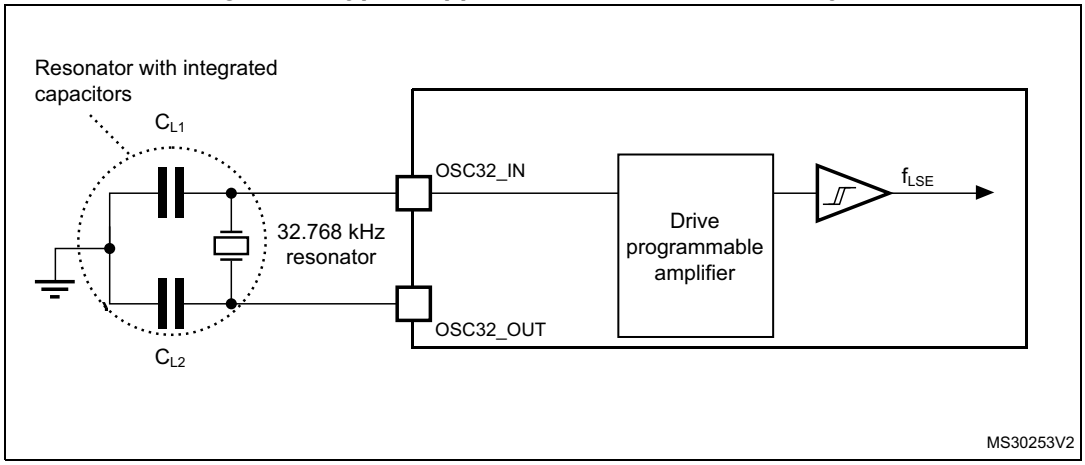
Figure 18. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between OSC32_IN and OSC32_OUT and it is forbidden to add one.

6.3.8 Internal clock source characteristics

The parameters given in *Table 41* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*. The provided curves are characterization results, not tested in production.

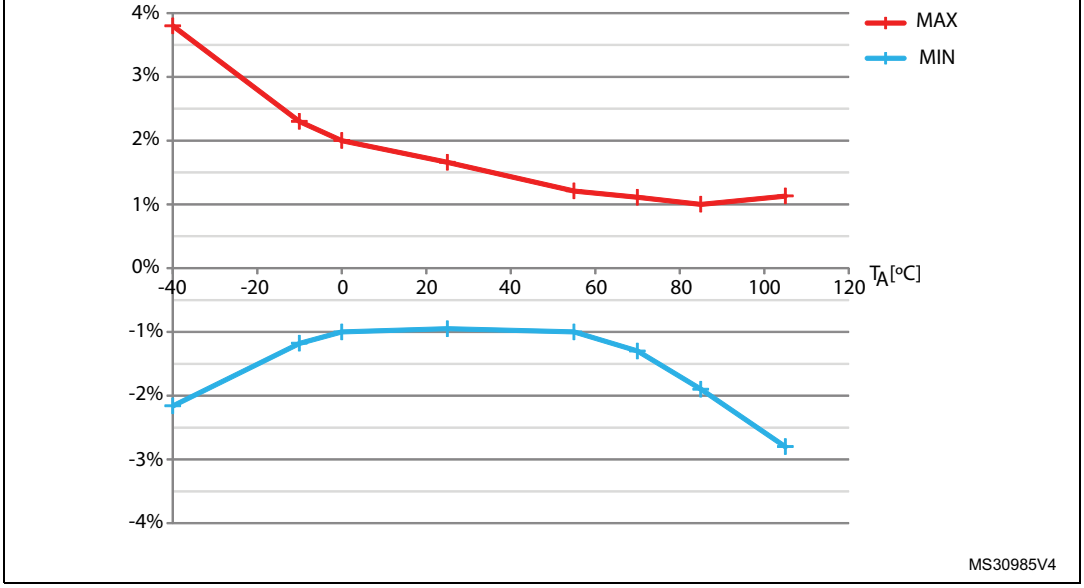
High-speed internal (HSI) RC oscillator

Table 41. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
TRIM	HSI user trimming step	-	-	-	1(2)	%
$DuCy_{(HSI)}$	Duty cycle	-	45(2)	-	55(2)	%
ACC_{HSI}	Accuracy of the HSI oscillator	T_A = -40 to 105°C	-2.8(3)	-	3.8(3)	%
		T_A = -10 to 85°C	-1.9(3)	-	2.3(3)	
		T_A = 0 to 85°C	-1.9(3)	-	2(3)	
		T_A = 0 to 70°C	-1.3(3)	-	2(3)	
		T_A = 0 to 55°C	-1(3)	-	2(3)	
		T_A = 25°C(4)	-1	-	1	
$t_{su(HSI)}$	HSI oscillator startup time	-	1(2)	-	2(2)	µs
$I_{DDA(HSI)}$	HSI oscillator power consumption	-	-	80	100(2)	µA

1. V_{DDA} = 3.3 V, T_A = -40 to 105°C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Data based on characterization results, not tested in production.
4. Factory calibrated, parts not soldered.

Figure 19. HSI oscillator accuracy characterization results for soldered parts



Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/48 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	3	dBµV
			30 to 130 MHz	23	
			130 MHz to 1 GHz	15	
			EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 52. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	-0	NA	mA
	Injected current on PF1 pin (FTf pin)	-0	NA	
	Injected current on PC0 pin (TTA pin)	-0	+5	
	Injected current on PA4, PA5 pins with induced leakage current on adjacent pins less than -20 µA	-5	NA	
	Injected current on other FT and FTf pins	-5	NA	
	Injected current on all other TC, TTa and RST pins	-5	+5	

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 53* are derived from tests performed under the conditions summarized in *Table 24: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant.

Table 53. I/O static characteristics

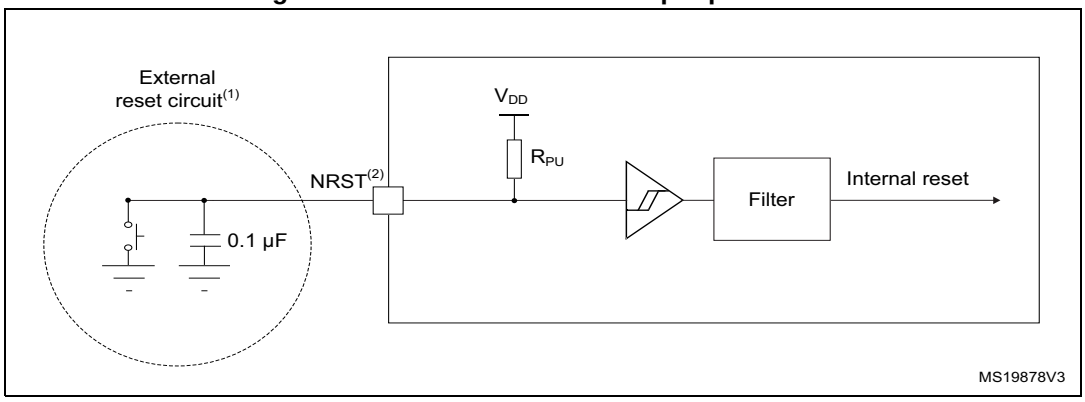
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	$0.3\ V_{DDIOx}+0.07$(1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DDIOx}-0.2$(1)	
		All I/Os	-	-	$0.3\ V_{DDIOx}$	
V_{IH}	High level input voltage	TC and TTa I/O	$0.445\ V_{DDIOx}+0.398$(1)	-	-	V
		FT and FTf I/O	$0.5\ V_{DDIOx}+0.2$(1)	-	-	
		All I/Os	$0.7\ V_{DDIOx}$	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200(1)	-	mV
		FT and FTf I/O	-	100(1)	-	
I_{lkg}	Input leakage current(2)	TC, FT and FTf I/O TTa in digital mode $V_{SS} \le V_{IN} \le V_{DDIOx}$	-	-	± 0.1	µA
		TTa in digital mode $V_{DDIOx} \le V_{IN} \le V_{DDA}$	-	-	1	
		TTa in analog mode $V_{SS} \le V_{IN} \le V_{DDA}$	-	-	± 0.2	
		FT and FTf I/O $V_{DDIOx} \le V_{IN} \le 5$ V	-	-	10	

Table 56. NRST pin characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{hys(NRST)}$	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R_{PU}	Weak pull-up equivalent resistor(2)	$V_{IN} = V_{SS}$	25	40	55	kΩ
$V_{F(NRST)}$	NRST input filtered pulse	-	-	-	100(1)	ns
$V_{NF(NRST)}$	NRST input not filtered pulse	$2.7 < V_{DD} < 3.6$	300(3)	-	-	ns
		$2.0 < V_{DD} < 3.6$	500(3)	-	-	

1. Data based on design simulation only. Not tested in production.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).
3. Data based on design simulation only. Not tested in production.

Figure 25. Recommended NRST pin protection



1. The external capacitor protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 56: NRST pin characteristics*. Otherwise the reset will not be taken into account by the device.

6.3.16 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 57* are derived from tests performed under the conditions summarized in *Table 24: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 57. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage for ADC ON	-	2.4	-	3.6	V
$I_{DDA\ (ADC)}$	Current consumption of the ADC(1)	$V_{DDA} = 3.3$ V	-	0.9	-	mA
f_{ADC}	ADC clock frequency	-	0.6	-	14	MHz
f_S(2)	Sampling rate	12-bit resolution	0.043	-	1	MHz

Table 57. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{TRIG} (2)	External trigger frequency	f_{ADC} = 14 MHz, 12-bit resolution	-	-	823	kHz
		12-bit resolution	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range	-	0	-	V_{DDA}	V
R_{AIN} (2)	External input impedance	See *Equation 1* and *Table 58* for details	-	-	50	kΩ
R_{ADC} (2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC} (2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL} (2)(3)	Calibration time	f_{ADC} = 14 MHz	5.9			µs
		-	83			$1/f_{ADC}$
$W_{LATENCY}$ (2)(4)	ADC_DR register ready latency	ADC clock = HSI14	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr} (2)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2 = 14$ MHz	0.196			µs
		$f_{ADC} = f_{PCLK}/2$	5.5			$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4 = 12$ MHz	0.219			µs
		$f_{ADC} = f_{PCLK}/4$	10.5			$1/f_{PCLK}$
		$f_{ADC} = f_{HSI14}$ = 14 MHz	0.179	-	0.250	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI14}$	-	1	-	$1/f_{HSI14}$
t_S (2)	Sampling time	f_{ADC} = 14 MHz	0.107	-	17.1	µs
		-	1.5	-	239.5	$1/f_{ADC}$
t_{STAB} (2)	Stabilization time	-	14			$1/f_{ADC}$
t_{CONV} (2)	Total conversion time (including sampling time)	f_{ADC} = 14 MHz, 12-bit resolution	1	-	18	µs
		12-bit resolution	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. During conversion of the sampled value (12.5 x ADC clock period), an additional consumption of 100 µA on I_{DDA} and 60 µA on I_{DD} should be taken into account.
2. Guaranteed by design, not tested in production.
3. Specified value includes only ADC timing. It does not include the latency of the register access.
4. This parameter specify latency for transfer of the conversion result to the ADC_DR register. EOC flag is set at this time.

Table 60. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Gain error(3)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(3)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(3)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(3)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. Guaranteed by design, not tested in production.
2. The DAC is in “quiescent mode” when it keeps the value steady on the output so no dynamic consumption is involved.
3. Data based on characterization results, not tested in production.

6.3.19 Temperature sensor characteristics

Table 62. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L (1)	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{30}	Voltage at 30 °C (± 5 °C)(2)	1.34	1.43	1.52	V
t_{START} (1)	ADC_IN16 buffer startup time	-	-	10	µs
t_{S_temp} (1)	ADC sampling time when reading the temperature	4	-	-	µs

1. Guaranteed by design, not tested in production.
2. Measured at V_{DDA} = 3.3 V ± 10 mV. The V_{30} ADC conversion result is stored in the TS_CAL1 byte. Refer to *Table 3: Temperature sensor calibration values*.

6.3.20 V_{BAT} monitoring characteristics

Table 63. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	2 x 50	-	kΩ
Q	Ratio on V_{BAT} measurement	-	2	-	-
Er(1)	Error on Q	–1	-	+1	%
t_{S_vbat} (1)	ADC sampling time when reading the V_{BAT}	4	-	-	µs

1. Guaranteed by design, not tested in production.

6.3.21 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 64. TIMx characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	20.8	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	-	$f_{TIMxCLK}/2$	-	MHz
		$f_{TIMxCLK}$ = 48 MHz	-	24	-	MHz
t_{MAX_COUNT}	16-bit timer maximum period	-	-	2^{16}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	1365	-	µs
	32-bit counter maximum period	-	-	2^{32}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	89.48	-	s

Table 67. I²C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum width of spikes that are suppressed by the analog filter	50(2)	260(3)	ns

1. Guaranteed by design, not tested in production.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

SPI/I²S characteristics

Unless otherwise specified, the parameters given in *Table 68* for SPI or in *Table 69* for I²S are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in *Table 24: General operating conditions*.

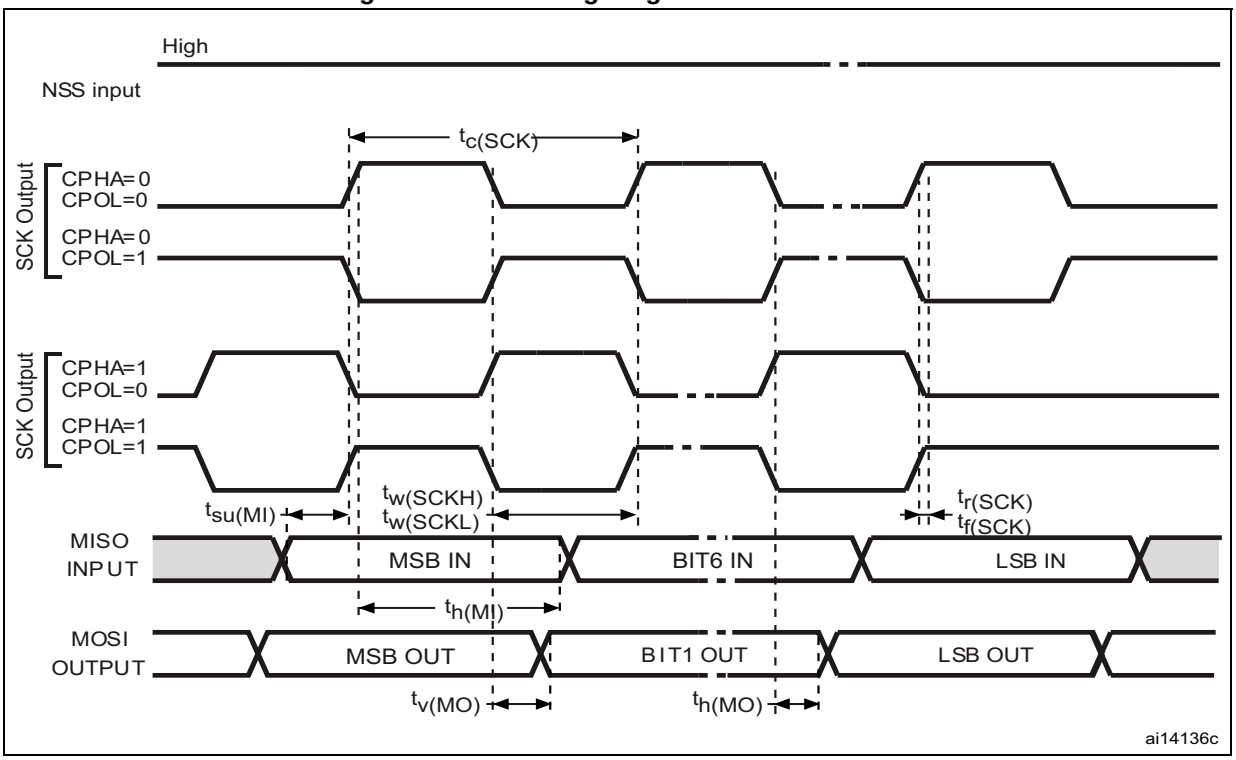
Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 68. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 15 pF	-	6	ns
$t_{su(NSS)}$	NSS setup time	Slave mode	4Tpclk	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode	2Tpclk + 10	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode, f_{PCLK} = 36 MHz, presc = 4	Tpclk/2 -2	Tpclk/2 + 1	
$t_{su(MI)}$ $t_{su(SI)}$	Data input setup time	Master mode	4	-	
		Slave mode	5	-	
$t_{h(MI)}$	Data input hold time	Master mode	4	-	
$t_{h(SI)}$		Slave mode	5	-	
$t_{a(SO)}$(2)	Data output access time	Slave mode, f_{PCLK} = 20 MHz	0	3Tpclk	
$t_{dis(SO)}$(3)	Data output disable time	Slave mode	0	18	
$t_{v(SO)}$	Data output valid time	Slave mode (after enable edge)	-	22.5	
$t_{v(MO)}$	Data output valid time	Master mode (after enable edge)	-	6	
$t_{h(SO)}$	Data output hold time	Slave mode (after enable edge)	11.5	-	
$t_{h(MO)}$		Master mode (after enable edge)	2	-	
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	25	75	%

1. Data based on characterization results, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 30. SPI timing diagram - master mode



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

Table 69. I^2S characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f_{CK} $1/t_{c(CK)}$	I^2S clock frequency	Master mode (data: 16 bits, Audio frequency = 48 kHz)	1.597	1.601	MHz
		Slave mode	0	6.5	
$t_{r(CK)}$	I^2S clock rise time	Capacitive load C_L = 15 pF	-	10	ns
$t_{f(CK)}$	I^2S clock fall time		-	12	
$t_{w(CKH)}$	I^2S clock high time	Master f_{PCLK}= 16 MHz, audio frequency = 48 kHz	306	-	
$t_{w(CKL)}$	I^2S clock low time		312	-	
$t_{v(WS)}$	WS valid time	Master mode	2	-	
$t_{h(WS)}$	WS hold time	Master mode	2	-	
$t_{su(WS)}$	WS setup time	Slave mode	7	-	
$t_{h(WS)}$	WS hold time	Slave mode	0	-	
DuCy(SCK)	I^2S slave input clock duty cycle	Slave mode	25	75	%

Table 73. UFBGA64 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 40. Recommended footprint for UFBGA64 package

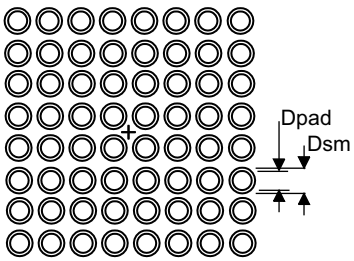


Table 74. UFBGA64 recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm